



**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.25	° C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	120	° C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	° C

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.7	2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
Static Drain-source On Resistance		$V_{GS}=10V, I_D=30A$		3.3	4	m $\Omega$
		$V_{GS}=4.5V, I_D=20A$		5	6	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=20A$		18		s
Source-drain voltage	$V_{SD}$	$I_S=30A$			1.28	V

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz$	-	2900	-	pF
Output capacitance	$C_{oss}$		-	880	-	
Reverse transfer capacitance	$C_{rss}$		-	105	-	

**Gate Charge characteristics( $T_a = 25^\circ C$ )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD}=30V$	-	35	-	nC
Gate - Source charge	$Q_{gs}$	$I_D=20A$	-	10	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS}=10V$	-	11	-	

Note: ① 1 1% ;





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Unit mm

SYMBOL	mi n	max	SYMBOL	mi n	max
A	2.10	2.50	D	6.35	6.80
A1	0.95	1.30	D1	5.10	5.50
B	0.80	1.25	E	5.30	6.30
b	0.50	0.80	e	2.24	2.35
b1	0.70	0.90	E1	4.43	4.73
c	0.45	0.60	L	7.00	9.40
c1	0.45	0.60			

